

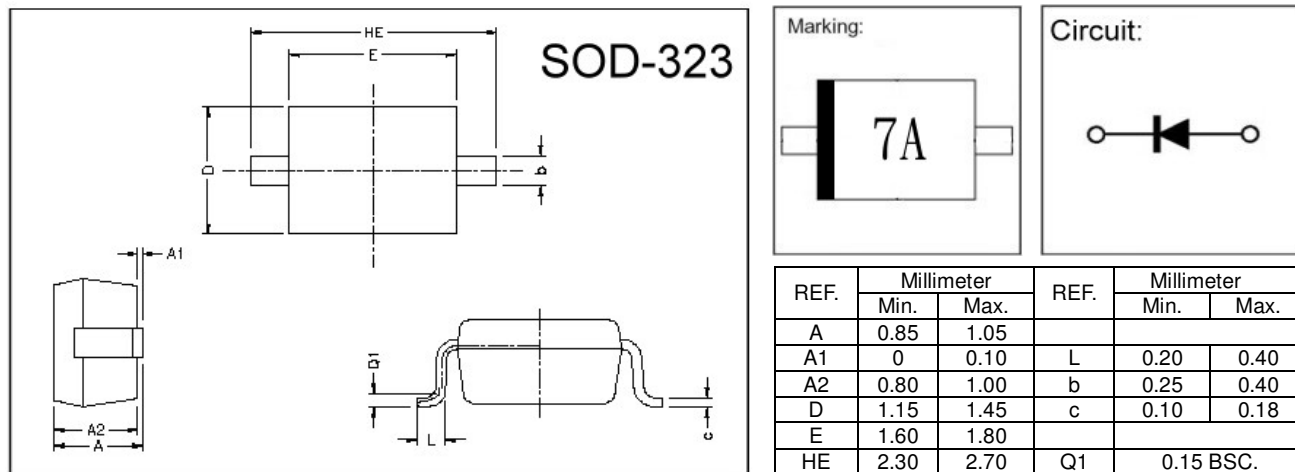
## GD751SD

**SURFACE MOUNT, SCHOTTKY BARRIER DIODE**  
**VOLTAGE 40V, CURRENT 0.03A**

### Description

The GD751SD is designed for high speed switching for detection and high reliability.

### Package Dimensions



### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>j</sub>	+125	°C
Storage Temperature	T <sub>stg</sub>	-40 ~ +125	°C
Maximum Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	40	V
Maximum RMS Voltage	V <sub>RMS</sub>	28	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I <sub>FSM</sub>	0.2	A
Typical Junction Capacitance between Terminal (Note 1)	C <sub>J</sub>	2.0	pF
Maximum Average Forward Rectified Current	I <sub>o</sub>	0.03	A
Total Power Dissipation	PD	225	mW

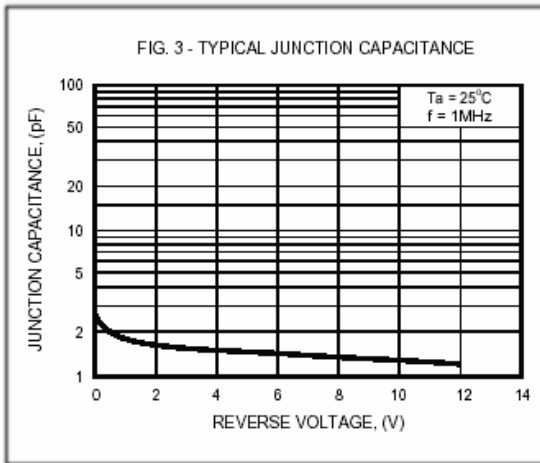
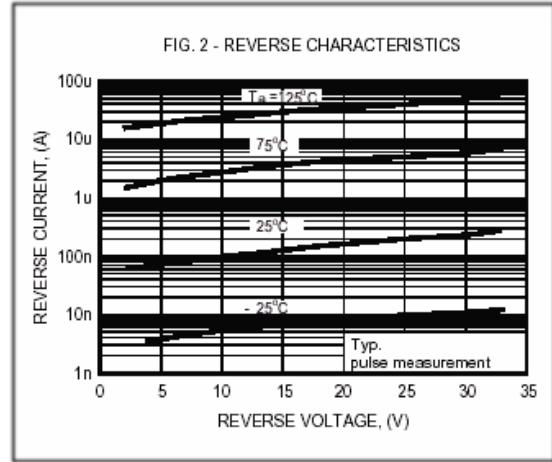
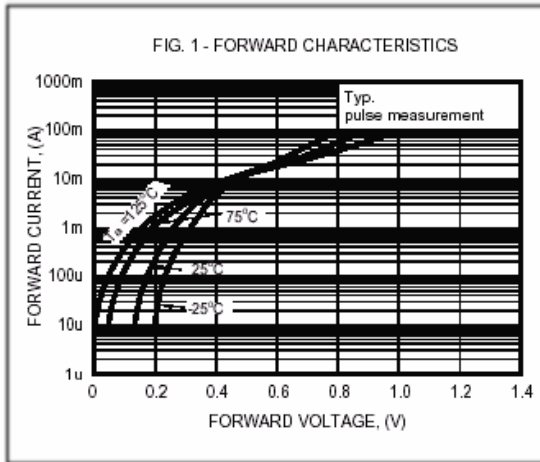
### Characteristics at Ta = 25°C

Characteristics	Symbol	Max	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V <sub>F</sub>	0.37	V	I <sub>F</sub> = 1mA
Maximum Average Reverse Current	I <sub>R</sub>	0.5	uA	V <sub>R</sub> = 30V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 1.0 volt.

2. ESD sensitive product handling required.

## Characteristics Curve



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